Siyuan Yu

List of Publications by Year
in descending order

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246	1,751	361045	500791
papers	citations	20 h-index	28 g-index

246	246	246	1160
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Repetitive Unclamped-Inductive-Switching-Induced Electrical Parameters Degradations and Simulation Optimizations for 4H-SiC MOSFETs. IEEE Transactions on Electron Devices, 2016, 63, 4331-4338.	1.6	61
2	Comprehensive Investigations on Degradations of Dynamic Characteristics for SiC Power <sc>MOSFET</sc>s Under Repetitive Avalanche Shocks. IEEE Transactions on Power Electronics, 2019, 34, 2748-2757.	5.4	45
3	Comprehensive Analysis of Electrical Parameters Degradations for SiC Power MOSFETs Under Repetitive Short-Circuit Stress. IEEE Transactions on Electron Devices, 2018, 65, 5440-5447.	1.6	42
4	Investigations on the Degradations of Double-Trench SiC Power MOSFETs Under Repetitive Avalanche Stress. IEEE Transactions on Electron Devices, 2019, 66, 546-552.	1.6	38
5	Further Study of the U-Shaped Channel SOI-LIGBT With Enhanced Current Density for High-Voltage Monolithic ICs. IEEE Transactions on Electron Devices, 2016, 63, 1161-1167.	1.6	37
6	Electrical Characteristic Study of an SOI-LIGBT With Segmented Trenches in the Anode Region. IEEE Transactions on Electron Devices, 2016, 63, 2003-2008.	1.6	37
7	Fast Computation of Radial Vibration in Switched Reluctance Motors. IEEE Transactions on Industrial Electronics, 2018, 65, 4588-4598.	5.2	37
8	A Low-Cost Constant Current Control Method for DCM and CCM in Digitally Controlled Primary-Side Regulation Flyback Converter. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2018, 6, 1483-1494.	3.7	31
9	Accurate model of switched reluctance motor based on indirect measurement method and least square support vector machine. IET Electric Power Applications, 2016, 10, 916-922.	1.1	29
10	A Novel Silicon-on-Insulator Lateral Insulated-Gate Bipolar Transistor With Dual Trenches for Three-Phase Single Chip Inverter ICs. IEEE Electron Device Letters, 2015, 36, 693-695.	2.2	28
11	Resonance Reduction by Optimal Switch Angle Selection in Switched Reluctance Motor. IEEE Transactions on Industrial Electronics, 2020, 67, 1867-1877.	5.2	28
12	A Two-Stage Buckâ€“Boost Integrated LLC Converter With Extended ZVS Range and Reduced Conduction Loss for High-Frequency and High-Efficiency Applications. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 727-743.	3.7	28
13	A Review on Hot-Carrier-Induced Degradation of Lateral DMOS Transistor. IEEE Transactions on Device and Materials Reliability, 2018, 18, 298-312.	1.5	26
14	Repetitive-Avalanche-Induced Electrical Parameters Shift for 4H-SiC Junction Barrier Schottky Diode. IEEE Transactions on Electron Devices, 2015, 62, 601-605.	1.6	25
15	A Single-Switched High-Switching-Frequency Quasi-Resonant Flyback Converter. IEEE Transactions on Power Electronics, 2019, 34, 8775-8786.	5.4	25
16	Interfacial damage extraction method for SiC power MOSFETs based on C-V characteristics. , 2017, , .		24
17	Understanding Short-Circuit Failure Mechanism of Double-Trench SiC Power MOSFETs. IEEE Transactions on Electron Devices, 2020, 67, 5593-5599.	1.6	23
18	Novel Digital Control Method for Improving Dynamic Responses of Multimode Primary-Side Regulation Flyback Converter. IEEE Transactions on Power Electronics, 2017, 32, 1457-1468.	5.4	22

#	Article	IF	Citations
19	A Ripple Control Dual-Mode Single-Inductor Dual-Output Buck Converter With Fast Transient Response. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2015, 23, 107-117.	2.1	21
20	Novel Snapback-Free Reverse-Conducting SOI-LIGBT With Dual Embedded Diodes. IEEE Transactions on Electron Devices, 2017, 64, 1187-1192.	1.6	21
21	Noise Immunity and its Temperature Characteristics Study of the Capacitive-Loaded Level Shift Circuit for High Voltage Gate Drive IC. IEEE Transactions on Industrial Electronics, 2018, 65, 3027-3034.	5.2	21
22	High precision constant voltage digital control scheme for primaryâ€side controlled flyback converter. IET Power Electronics, 2016, 9, 2522-2533.	1.5	19
23	Single Pulse Unclamped-Inductive-Switching Induced Failure and Analysis for 650 V p-GaN HEMT. IEEE Transactions on Power Electronics, 2020, 35, 11328-11331.	5.4	19
24	Method for radial vibration modelling in switched reluctance motor. IET Electric Power Applications, 2016, 10, 834-842.	1.1	17
25	Design and Fabrication of a Monolithic Optoelectronic Integrated Si CMOS LED Based on Hot-Carrier Effect. IEEE Journal of Selected Topics in Quantum Electronics, 2016, 22, 70-77.	1.9	17
26	Hot-Carrier-Induced Degradations and Optimizations for Lateral DMOS Transistor With Multiple Floating Poly-Gate Field Plates. IEEE Transactions on Electron Devices, 2017, 64, 3275-3281.	1.6	17
27	Comparison Investigations on Unclamped-Inductive-Switching Behaviors of Power GaN Switching Devices. IEEE Transactions on Industrial Electronics, 2022, 69, 5041-5049.	5.2	17
28	A capacitive-loaded level shift circuit for improving the noise immunity of high voltage gate drive IC. , 2015, , .		16
29	A U-Shaped Channel SOI-LIGBT With Dual Trenches. IEEE Transactions on Electron Devices, 2017, 64, 2587-2591.	1.6	16
30	A Digital Control Scheme for PSR Flyback Converter in CCM and DCM. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2020, 8, 2837-2849.	3.7	16
31	The Investigation of Electrothermal Characteristics of High-Voltage Lateral IGBT for ESD Protection. IEEE Transactions on Device and Materials Reliability, 2012, 12, 146-151.	1.5	15
32	A Novel Compact High-Voltage LDMOS Transistor Model for Circuit Simulation. IEEE Transactions on Electron Devices, 2013, 60, 346-353.	1.6	15
33	Low-Loss SOI-LIGBT With Dual Deep-Oxide Trenches. IEEE Transactions on Electron Devices, 2017, 64, 3282-3286.	1.6	15
34	Low-Loss SOI-LIGBT With Triple Deep-Oxide Trenches. IEEE Transactions on Electron Devices, 2017, 64, 3756-3761.	1.6	15
35	Power loss analysis of active clamp forward converter in continuous conduction mode and discontinuous conduction mode operating modes. IET Power Electronics, 2013, 6, 1142-1150.	1.5	14
36	Analysis of simulation of multiterminal electro-optic modulator based on p-n junction in reverse bias. Optical Engineering, 2015, 54, 057104.	0.5	14

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37	Digital regulation scheme for multimode primaryâ€side controlled flyback converter. IET Power Electronics, 2016, 9, 782-788.	1.5	14
38	An Integrated Bootstrap Diode Emulator for 600-V High Voltage Gate Drive IC With P-Sub/P-Epi Technology. IEEE Transactions on Power Electronics, 2016, 31, 518-523.	5.4	14
39	A Novel Lateral DMOS Transistor With H-Shape Shallow-Trench-Isolation Structure. IEEE Transactions on Electron Devices, 2018, 65, 5218-5221.	1.6	14
40	Sampled-Data Modeling for PCM and ZVS Controlled Critical Conduction Mode (CrCM) Active Clamp Flyback (ACF) Converter at Variable Switching Frequency. IEEE Transactions on Circuits and Systems I: Regular Papers, 2020, 67, 3588-3600.	3.5	14
41	Electrical Characteristic Investigation on a Novel Double-Well Isolation Structure in 600-V-Class High-Voltage Integrated Circuits. IEEE Transactions on Electron Devices, 2012, 59, 3477-3481.	1.6	13
42	Investigation on degradation mechanism and optimization for SiC power MOSFETs under long-term short-circuit stress. , 2018, , .		13
43	Single-Pulse Avalanche Failure Investigations of Si-SJ-mosfet and SiC-mosfet by Step-Control Infrared Thermography Method. IEEE Transactions on Power Electronics, 2020, 35, 5180-5189.	5.4	13
44	Hot-Carrier-Induced On-Resistance Degradation of n-Type Lateral DMOS Transistor With Shallow Trench Isolation for High-Side Application. IEEE Transactions on Device and Materials Reliability, 2015, 15, 458-460.	1.5	12
45	A high frequency isolated resonant gate driver for SiC power MOSFET with asymmetrical ON/OFF voltage. , 2017, , .		12
46	Influence of switch angles on secondâ€order current harmonic and resonance in switched reluctance motors. IET Electric Power Applications, 2018, 12, 1247-1255.	1.1	12
47	Small Signal Modeling and Control Loop Design of Critical Conduction Mode Active Clamp Flyback Converter. IEEE Transactions on Power Electronics, 2021, 36, 7250-7263.	5.4	12
48	Simulation Study of A 1200V 4H-SiC Lateral MOSFET With Reduced Saturation Current. IEEE Electron Device Letters, 2021, 42, 1037-1040.	2.2	12
49	TC-LIGBTs on the Thin Sol Layer for the High Voltage Monolithic ICs With High Current Density and Latch-Up Immunity. IEEE Transactions on Electron Devices, 2014, 61, 3814-3820.	1.6	11
50	Isolated gate driver for SiC MOSFETs with constant negative off voltage. , 2017, , .		11
51	Investigation on Self-Adjust Conductivity Modulation SOI-LIGBT Structure (SCM-LIGBT) for Monolithic High-Voltage IC. IEEE Transactions on Electron Devices, 2017, 64, 3762-3767.	1.6	11
52	Lateral DMOS With Partial-Resist-Implanted Drift Region for Alleviating Hot-Carrier Effect. IEEE Transactions on Device and Materials Reliability, 2017, 17, 780-784.	1.5	11
53	A New Modulation Strategy for Four-switch Buck-boost Converter with Reduced Freewheeling Current. , 2020, , .		11
54	Super Field Plate Technique That Can Provide Charge Balance Effect for Lateral Power Devices Without Occupying Drift Region. IEEE Transactions on Electron Devices, 2020, 67, 2218-2222.	1.6	11

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55	Investigations of inhomogeneous reverse recovery behavior of the body diode in superjunction MOSFET. , 2017, , .		10
56	A Phase-Shift Triple Full-Bridge Converter With Three Shared Leading Legs. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2018, 6, 1912-1920.	3.7	10
57	Verification of Single-Pulse Avalanche Failure Mechanism for Double-Trench SiC Power MOSFETs. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 2190-2200.	3.7	10
58	High-Voltage a-IGZO TFTs With the Stair Gate-Dielectric Structure. IEEE Transactions on Electron Devices, 2021, 68, 4462-4466.	1.6	10
59	Off-State Stress Degradation Analysis and Optimization for the High-Voltage SOI-pLEDMOS With Thick Gate Oxide. IEEE Transactions on Electron Devices, 2013, 60, 3632-3638.	1.6	9
60	A High-Frequency Model for a PCM Buck Converter. IEEE Transactions on Power Electronics, 2015, 30, 2304-2312.	5.4	9
61	Electrical Parameters Degradations and Optimizations of SOI-LIGBT Under Repetitive Unclamped-Inductive-Switching Conditions. IEEE Transactions on Electron Devices, 2016, 63, 1644-1649.	1.6	9
62	Analysis of a Time-Length Compensation Algorithm for Elimination of Subharmonic Oscillation and Application in a Digitally Controlled Primary-Side Regulation Flyback Converter. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2017, 5, 1710-1719.	3.7	9
63	Mechanism and Novel Structure for di/dt Controllability in U-Shaped Channel Silicon-on-Insulator Lateral IGBTs. IEEE Electron Device Letters, 2019, 40, 1658-1661.	2.2	9
64	Complete Avalanche Process and Failure Mechanism of Trench-Gate FS-IGBT Under Unclamped Inductive Switching by Using Infrared Visualization Method. IEEE Transactions on Electron Devices, 2020, 67, 3908-3911.	1.6	9
65	Investigations on Electrical Parameters Degradations of p-GaN HEMTs Under Repetitive UIS Stresses. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 2227-2234.	3.7	9
66	Investigation on the Degradation Mechanism for SiC Power MOSFETs Under Repetitive Switching Stress. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 2180-2189.	3.7	9
67	A Novel Digital Control Method of Primary-Side Regulated Flyback With Active Clamping Technique. IEEE Transactions on Circuits and Systems I: Regular Papers, 2021, 68, 950-962.	3.5	9
68	A 400-V Half Bridge Gate Driver for Normally-Off GaN HEMTs With Effective Dv/Dt Control and High Dv/Dt Immunity. IEEE Transactions on Industrial Electronics, 2023, 70, 741-751.	5.2	9
69	Peripheral Adaption Power Cell Network for High Efficiency and High Linearity Power Amplifier. IEEE Microwave and Wireless Components Letters, 2014, 24, 799-801.	2.0	8
70	Transient response optimisation for peak current mode buck converter in the application of dynamic voltage scaling. IET Power Electronics, 2014, 7, 705-712.	1.5	8
71	Hot-Carrier-Induced Forward and Reverse Saturation Current Degradations for the n-Type Symmetric EDMOS Transistor. IEEE Electron Device Letters, 2014, 35, 690-692.	2.2	8
72	A Robust W-Shape-Buffer LIGBT Device With Large Current Capability. IEEE Transactions on Power Electronics, 2014, 29, 4466-4469.	5.4	8

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73	Analysis of commonâ€mode electromagnetic interference noise in a flyback converter using a selfâ€supply power control integrated circuit. IET Power Electronics, 2015, 8, 1749-1757.	1.5	8
74	Dynamic characteristics analysis of 1.2kV SiC VDMOS under high temperature up to 375Â°C. , 2017, , .		8
75	New digital control method for improving dynamic response of synchronous rectified flyback converter with CCM and DCM mode. , 2018, , .		8
76	A single-switched high-switching-frequency quasi-resonant flyback converter with zero-current-switching and valley-switching. , 2019, , .		8
77	Comprehensive Investigation on Electrical Properties of nLDMOS and pLDMOS Under Mechanical Strain. IEEE Transactions on Electron Devices, 2019, 66, 1012-1017.	1.6	8
78	Optimal Phase Shift Control Strategy of Buck-Boost Integrated LLC Converter Achieving Wide Input Voltage Range, MHz-frequency and High Efficiency. , 2020, , .		8
79	Highâ€temperature electrical performances and physicsâ€based analysis of pâ€GaN HEMT device. IET Power Electronics, 2020, 13, 420-425.	1.5	8
80	Modeling Avalanche Induced Degradation for 4H-SiC Power MOSFETs. IEEE Transactions on Power Electronics, 2020, 35, 11299-11303.	5.4	8
81	An Improved Adaptive Synchronous Rectification Method with the Enhanced Capacity to Eliminate Reverse Current. IEEE Transactions on Power Electronics, 2021, , 1-1.	5.4	8
82	Anomalous Hot-Carrier-Induced Linear Drain Current Degradation of LDMOS Under Pulse Gate Stress With Different Amplitudes. IEEE Electron Device Letters, 2013, 34, 786-788.	2.2	7
83	Analysis and accurate modeling of a flyback converter on conducted EMI. , 2015, , .		7
84	An accurate design method of RCD circuit for flyback converter considering diode reverse recovery. , 2016, , .		7
85	A novel high-voltage interconnection structure with dual trenches for 500V SOI-LIGBT. , 2016, , .		7
86	Bipolar gate drive integrated circuit for insulated gate bipolar transistor to achieve better tradeoff between the turnâ€off losses and collector voltage overshoot. IET Circuits, Devices and Systems, 2016, 10, 410-416.	0.9	7
87	An Improved Convergent Model for Single-Photon Avalanche Diodes. IEEE Photonics Technology Letters, 2017, 29, 798-801.	1.3	7
88	Novel Hybrid Analytical/Numerical Conducted EMI Model of a Flyback Converter. IEEE Transactions on Electromagnetic Compatibility, 2017, 59, 488-497.	1.4	7
89	A simple average current control with timeâ€length equality for primaryâ€side regulation flyback converter with constant output current control. International Journal of Circuit Theory and Applications, 2018, 46, 2477-2494.	1.3	7
90	Study and Implementation of 600-V High-Voltage Gate Driver IC With the Common-Mode Dual-Interlock Technique for GaN Devices. IEEE Transactions on Industrial Electronics, 2021, 68, 1506-1514.	5.2	7

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91	700V thin SOI-LIGBT with high current capability. , 2013, , .		6
92	Negative voltage surge resistant circuit design in HVIC. Electronics Letters, 2013, 49, 1476-1477.	0.5	6
93	Anomalous output characteristic shift for the n-type lateral diffused metal-oxide-semiconductor transistor with floating P-top layer. Applied Physics Letters, 2014, 104, .	1.5	6
94	An electrolytic capacitorâ€less LED driver with interleaving flyback topology. International Journal of Circuit Theory and Applications, 2015, 43, 2025-2038.	1.3	6
95	Hybrid modulation scheme for dual active bridge converter that employs the triangular modulation and the single phase shift modulation. International Journal of Circuit Theory and Applications, 2016, 44, 1982-2002.	1.3	6
96	Investigation on Hot-Carrier-Induced degradation of STI-nLDMOS with two-step-oxide process for high side application. , 2016, , .		6
97	Comparative Study on Vibration Mode with Different Current Amplitudes and Modeling of Radial Vibration in Switched Reluctance Motor. , 2018, , .		6
98	Comprehensive investigation on mechanical strain induced performance boosts in LDMOS. , 2018, , .		6
99	64 Ã— 64 GM-APD array-based readout integrated circuit for 3D imaging applications. Science China Information Sciences, 2019, 62, 1.	2.7	6
100	Experimental Investigation on the Electrical Properties of Lateral IGBT Under Mechanical Strain. IEEE Electron Device Letters, 2019, 40, 937-940.	2.2	6
101	Reliability Concerns on LDMOS With Different Split-STI Layout Patterns. IEEE Transactions on Electron Devices, 2020, 67, 185-192.	1.6	6
102	Quasisaturation Effect and Optimization for 4H-SiC Trench MOSFET With P+ Shielding Region. IEEE Transactions on Electron Devices, 2021, 68, 4550-4556.	1.6	6
103	Understanding Electrical Parameter Degradations of P-GaN HEMT Under Repetitive Short-Circuit Stresses. IEEE Transactions on Power Electronics, 2021, 36, 12173-12176.	5.4	6
104	A novel double-well isolation structure for high voltage ICs. , 2012, , .		5
105	Linear Drain Current Degradation of ps-LDMOS Transistor Under ${m I}_{m submax}$ and ${m I}_{m gmax}$ Stress. IEEE Electron Device Letters, 2013, 34, 1032-1034.	2.2	5
106	Novel 200V power devices with large current capability and high reliability by inverted HV-well SOI technology. , 2013, , .		5
107	Investigation on Electrical Degradation of High Voltage nLDMOS After High Temperature Reverse Bias Stress. IEEE Transactions on Device and Materials Reliability, 2014, 14, 651-656.	1.5	5
108	Zeroâ€steadyâ€stateâ€error compensation method in application of peak current mode buck converter with fast transient response. IET Power Electronics, 2015, 8, 647-655.	1.5	5

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109	Hot-Carrier-Induced Degradations Investigations for 600 V SOI-LIGBT by an Improved Charge Pumping Solution. IEEE Transactions on Electron Devices, 2017, 64, 634-637.	1.6	5
110	Mobility Fluctuation-Induced Low-Frequency Noise in Ultrascaled Ge Nanowire nMOSFETs With Near-Ballistic Transport. IEEE Transactions on Electron Devices, 2018, 65, 2573-2577.	1.6	5
111	Influence of Latch-Up Immunity Structure on ESD Robustness of SOI-LIGBT Used As Output Device. IEEE Transactions on Device and Materials Reliability, 2018, 18, 284-290.	1.5	5
112	A 600V high-side gate drive circuit with ultra-low propagation delay for enhancement mode GaN devices. , 2018, , .		5
113	An Integrated Bias Voltage Control Method for SPAD Arrays. IEEE Photonics Technology Letters, 2018, 30, 1723-1726.	1.3	5
114	Switch-OFF Avalanche-Breakdown-Induced Electrical Degradations of RF-LDMOS Transistor for SMPAs Applications. IEEE Transactions on Electron Devices, 2018, 65, 4719-4723.	1.6	5
115	ZVS Buck-Boost LLC cascade converter with all soft switched switches. International Journal of Electronics, 2019, 106, 895-911.	0.9	5
116	Hot-Carrier-Induced Degradation and Optimization for 700-V High-Voltage Lateral DMOS by the AC Stress. IEEE Transactions on Electron Devices, 2020, 67, 1090-1097.	1.6	5
117	New Digital Control Method for Improving Dynamic Response of Synchronous Rectified PSR Flyback Converter With CCM and DCM Modes. IEEE Transactions on Power Electronics, 2020, 35, 12347-12358.	5.4	5
118	Silicon-on-Insulator Lateral DMOS With Potential Modulation Plates and Multiple Deep-Oxide Trenches. IEEE Transactions on Electron Devices, 2021, 68, 5073-5077.	1.6	5
119	A Silicon-On-Insulator Lateral IGBT With Segmented Trenches for Improving Short-Circuit Withstanding Capability. IEEE Transactions on Electron Devices, 2022, 69, 4042-4045.	1.6	5
120	400-V Amorphous IGZO Thin-Film Transistors With Drift Region Doped by Hydrogen. IEEE Transactions on Electron Devices, 2022, 69, 3732-3736.	1.6	5
121	A 65nm 10MHz single-inductor dual-output switching buck converter with time-multiplexing control. , 2011, , .		4
122	A dual-mode single-inductor dual-output dc-dc converter with fast transient response. IEICE Electronics Express, 2012, 9, 1780-1785.	0.3	4
123	Lowâ€jitter, highâ€linearity currentâ€controlled complementary metal oxide semiconductor relaxation oscillator with optimised floating capacitors. IET Circuits, Devices and Systems, 2014, 8, 509-515.	0.9	4
124	Modeling and analysis of primary side regulated flyback converter with pulse frequency modulation. , 2015, , .		4
125	A Novel High Latch-Up Immunity Electrostatic Discharge Protection Device for Power Rail in High-Voltage ICs. IEEE Transactions on Device and Materials Reliability, 2016, 16, 266-268.	1.5	4
126	A novel digital multi-mode control strategy with PSM for primary-side flyback converter. International Journal of Electronics, 2017, 104, 840-854.	0.9	4

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127	Electrical Degradations of p-GaN HEMT under High Off-state Bias Stress with Negative Gate Voltage. , 2019, , .		4
128	Breakdown Voltage Walk-in Phenomenon and Optimization for the Trench-Gate p-Type VDMOS Under Single Avalanche Stress. IEEE Transactions on Electron Devices, 2020, 67, 2445-2450.	1.6	4
129	Investigation on the Degradation Mechanism for GaN Cascode Device Under Repetitive Hard-Switching Stress. IEEE Transactions on Power Electronics, 2022, 37, 6009-6017.	5.4	4
130	High Precision Primary Side Regulation Constant Voltage Control Method for Primary and Secondary Resonant Active Clamp Flyback Converter. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2022, 10, 6985-6999.	3.7	4
131	A novel surface potential-based mobility degradation model of thin-oxide-MOSFET for circuit simulation. , 2011, , .		3
132	Low power design for SoC with power management unit. , 2011, , .		3
133	Linear drain current degradations of FG-pLEDMOS transistor under different AC stress conditions. , 2012, , .		3
134	Model of hotâ€carrier degradation for lateral IGBT device on SOI substrate. Electronics Letters, 2013, 49, 497-499.	0.5	3
135	A novel digital controller for boost PFC converter with high power factor and fast dynamic response. , 2013, , .		3
136	1 ppm/Â°C bandgap with multipoint curvatureâ€compensation technique for HVIC. Electronics Letters, 2014, 50, 1908-1910.	0.5	3
137	A new digital predictive control strategy for boost PFC converter. IEICE Electronics Express, 2015, 12, 20150726-20150726.	0.3	3
138	Gateâ€drive circuit with efficient energy recovery based on DC/DC converter. Electronics Letters, 2016, 52, 952-954.	0.5	3
139	A LLC resonant converter with dual resonant frequency for high light load efficiency. International Journal of Electronics, 0, , 1-15.	0.9	3
140	A composite structure named self-adjusted conductivity modulation SOI-LIGBT with low on-state voltage. , 2017, , .		3
141	Study on EMI Characteristics of the Superjunction DMOS in Flyback Converter System. IEEE Transactions on Device and Materials Reliability, 2017, 17, 692-697.	1.5	3
142	Integrated GaN MIS-HEMT with Multi-Channel Heterojunction SBD Structures. , 2019, , .		3
143	Hot-Carrier-Induced Degradation and Optimization for Lateral DMOS With Split-STI-Structure in the Drift Region. IEEE Transactions on Electron Devices, 2019, 66, 2869-2875.	1.6	3
144	Experimental Investigation on the Electrical Properties of SOI-LIGBT Under Total-Ionizing-Dose Radiation. , 2020, , .		3

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145	System Performance Optimization for Dual-Loop Dual-Variable Controlled Active Clamp Flyback Converter Using Decoupling Compensation Technique. , 2021, , .		3
146	Performance Boosts in n-Type Lateral Double-Diffused MOSFET With Process-Induced Strain Using Contact Etch Stop Layer Stressor. IEEE Transactions on Electron Devices, 2021, 68, 421-424.	1.6	3
147	Comprehensive Investigation on Electrical Properties of Split-Gate Trench Power MOSFETs Under Mechanical Strains. IEEE Transactions on Electron Devices, 2022, 69, 1191-1195.	1.6	3
148	Numerical study of aÂnovel GaN vertical FinFET with aÂp-base structure for high switching performance. Journal of Computational Electronics, 2022, 21, 625-632.	1.3	3
149	Unclamped-Inductive-Switching Behaviors of p-GaN HEMTs at Cryogenic Temperature. IEEE Transactions on Power Electronics, 2022, 37, 11507-11510.	5.4	3
150	500 V dual gate deepâ€oxide trench SOIâ€LIGBT with improved shortâ€circuit immunity. Electronics Letters, 2015, 51, 78-80.	0.5	2
151	ESD failure mechanism and optimiztion for the LDMOS with low on-resistance and large geometric array used as output device. , 2016, , .		2
152	1200 V FSâ€IGBT with electric field modulation layer to improve tradeâ€off between avalanche ruggedness and onâ€state voltage drop. Electronics Letters, 2017, 53, 100-102.	0.5	2
153	A high linearity current-controlled CMOS relaxation oscillator with frequency self-calibration technique. Analog Integrated Circuits and Signal Processing, 2017, 92, 29-37.	0.9	2
154	Temperature compensated and gated CMOS ring oscillator for time-to-digital converter application. Analog Integrated Circuits and Signal Processing, 2017, 90, 513-521.	0.9	2
155	Electrical parameters shifts of 1.2kV 4H-SiC MOSFET under cosmic radiations. , 2017, , .		2
156	Influence of forward current freewheeling time on di/dt robustness of SJ-MOSFET body diode. , 2017, , .		2
157	Duty-cycle-accelerated hot-carrier degradation and lifetime evaluation for 700V lateral DMOS. , 2018, , .		2
158	An efficiency optimization method for a high frequency quasi-ZVS controlled resonant flyback converter. , 2019, , .		2
159	Impact of Depeltion in Substrate on Turn-off Characteristic of Superjunction SOI-LIGBT. , 2019, , .		2
160	Investigation of Electrical Parameters Degradations for 600V SOI-LIGBT under Repetitive ESD Stresses. , 2019, , .		2
161	Lightning Surge Robustness Analysis and Optimization for an LED Driver Based on a Flyback Converter. IEEE Transactions on Industrial Electronics, 2021, 68, 10449-10458.	5.2	2
162	Numerical Study of Novel GaN HEMTs With Integrated SBDs for Ultrahigh Reverse Conduction Capability. IEEE Transactions on Electron Devices, 2021, 68, 931-933.	1.6	2

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163	Hot-Carrier-Induced Reliability Concerns for Lateral DMOS Transistors with Split-STI Structures. , 2021, , .		2
164	Low On-Resistance SOI-LDMOS With Mobility-Enhancing Auxiliary Cell. , 2021, , .		2
165	Investigation on the Single-event Burnout and Hardening of the 500V SOI Lateral-IGBT. , 2021, , .		2
166	Degradation Investigations on Asymmetric Trench SiC Power MOSFETs Under Repetitive Unclamped Inductive Switching Stress. , 2021, , .		2
167	A High-Power-Density Four-switch Buck-boost Converter using 3D Multi-PCB Structure. , 2021, , .		2
168	Simulation Study of Novel Trench Gate U-Shaped Channel SOI Lateral IGBTs With Suppressed Gate Voltage Overshoot and Reduced di/dt. IEEE Transactions on Electron Devices, 2021, 68, 3930-3935.	1.6	2
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